

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	435	schottky and GaN and gate	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/09 13:32
L2	86	schottky and GaN and aluminum adj oxide	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/09 14:06
L5	23	GaN and thermal\$3 with aluminum adj oxide	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/09 14:22
L6	18	GaN with thermal\$3 near3 oxide	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/09 14:31
L7	9	gate same thermal\$3 near3 aluminum adj oxide	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/09 14:34
L9	40	gate adj insulat\$3 near3 aluminum adj oxide	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/09 14:36
L12	28	oxidizing with aluminum adj nitride with aluminum adj oxide	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/09 14:42
L16	181	aluminum adj oxide adj nitride	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/09 14:46

L24	6	gate adj insulat\$3 with gallium near1 oxide	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/09 15:25
L32	41	pd/Si or pd/ti	USPAT	OR	OFF	2005/06/09 15:54
S1	60	aluminum adj nitride same aluminum adj oxide same gate	USPAT	OR	OFF	2005/06/09 10:34
S3	50	aluminum adj nitride same aluminum adj oxide same gallium adj nitride	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/09 10:38
S6	245	schottky and aluminum adj oxide and semiconductor and gate	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/09 13:27